

Absolute Maximum Ratings

Stresses beyond the limits listed below may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

V_S 0V to +14V
 V_{IN} $-V_S - 0.5V$ to $+V_S + 0.5V$

Operating Conditions

Supply Voltage Range 2.5V to 12V
Operating Temperature Range -40°C to 125°C
Junction Temperature 150°C
Storage Temperature Range..... -65°C to 150°C
Lead Temperature (Soldering, 10s) 260°C

Package Thermal Resistance

θ_{JA} (TSOT-5) 215°C/W
 θ_{JA} (SOIC-8) 150°C/W
Package thermal resistance (θ_{JA}), JEDEC standard, multi-layer test boards, still air.

Electrical Characteristics at +3V

$T_A = 25^\circ\text{C}$, $V_S = +3\text{V}$, $R_f = 1\text{k}\Omega$, $R_L = 1\text{k}\Omega$ to $V_S/2$; $G = 2$; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Frequency Domain Response						
GBWP	-3dB Gain Bandwidth Product	G = 10, V _{OUT} = 0.05V _{pp}		31		MHz
UGBW	Unity Gain Bandwidth	V _{OUT} = 0.05V _{pp} , R _f = 0		50		MHz
BW _{SS}	-3dB Bandwidth	V _{OUT} = 0.05V _{pp}		24		MHz
BW _{LS}	Large Signal Bandwidth	V _{OUT} = 2V _{pp}		3.3		MHz
Time Domain						
t _R , t _F	Rise and Fall Time	V _{OUT} = 2V step; (10% to 90%)		150		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		78		ns
OS	Overshoot	V _{OUT} = 2V step		0.3		%
SR	Slew Rate	2V step		11		V/μs
Distortion/Noise Response						
HD2	2nd Harmonic Distortion	2V _{pp} , 10kHz, R _L = 1kΩ		-98		dBc
		2V _{pp} , 100kHz, R _L = 100Ω		-85		dBc
HD3	3rd Harmonic Distortion	2V _{pp} , 10kHz, R _L = 1kΩ		-95		dBc
		2V _{pp} , 100kHz, R _L = 100Ω		-81		dBc
THD	Total Harmonic Distortion	1V _{pp} , 1kHz, G = 1, R _L = 2kΩ		0.0005		%
e _n	Input Voltage Noise	>10kHz		5.5		nV/√Hz
		>100kHz		3.9		nV/√Hz
DC Performance						
V _{IO}	Input Offset Voltage			0.088		mV
d _{VIO}	Average Drift			1.3		μV/°C
I _B	Input Bias Current			-0.340		μA
dI _B	Average Drift			0.8		nA/°C
I _{OS}	Input Offset Current			0.2		μA
PSRR	Power Supply Rejection Ratio	DC		100		dB
A _{OL}	Open Loop Gain	V _{OUT} = V _S / 2		104		dB
I _S	Supply Current	per channel		1.85		mA
Input Characteristics						
R _{IN}	Input Resistance	Non-inverting, G = 1		30		MΩ
C _{IN}	Input Capacitance			1.1		pF
CMIR	Common Mode Input Range			-0.5 to 3.5		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = 0.5V to 2.5V		94		dB
Output Characteristics						
V _{OUT}	Output Swing	R _L = 150Ω		0.085 to 2.80		V
		R _L = 1kΩ		0.04 to 2.91		V
I _{OUT}	Output Current			+75, -40		mA
I _{SC}	Short Circuit Current	V _{OUT} = V _S / 2		+95, -50		mA

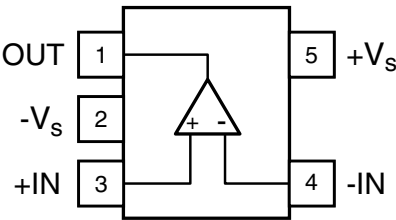
Electrical Characteristics at $\pm 5V$

$T_A = 25^\circ\text{C}$, $V_S = \pm 5V$, $R_f = 1k\Omega$, $R_L = 1k\Omega$ to GND; $G = 2$; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Frequency Domain Response						
GBWP	-3dB Gain Bandwidth Product	G = 10, V _{OUT} = 0.05V _{pp}		35		MHz
UGBW	Unity Gain Bandwidth	V _{OUT} = 0.05V _{pp} , R _f = 0		55		MHz
BW _{SS}	-3dB Bandwidth	V _{OUT} = 0.05V _{pp}		25		MHz
BW _{LS}	Large Signal Bandwidth	V _{OUT} = 2V _{pp}		3.6		MHz
Time Domain						
t _R , t _F	Rise and Fall Time	V _{OUT} = 2V step; (10% to 90%)		125		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		80		ns
OS	Overshoot	V _{OUT} = 2V step		0.3		%
SR	Slew Rate	4V step		12		V/μs
Distortion/Noise Response						
HD2	2nd Harmonic Distortion	2V _{pp} , 10kHz, R _L = 1kΩ		-125		dBc
		2V _{pp} , 100kHz, R _L = 100Ω		-90		dBc
HD3	3rd Harmonic Distortion	2V _{pp} , 10kHz, R _L = 1kΩ		-127		dBc
		2V _{pp} , 100kHz, R _L = 100Ω		-85		dBc
THD	Total Harmonic Distortion	1V _{pp} , 1kHz, G = 1, R _L = 2kΩ		0.00005		%
e _n	Input Voltage Noise	>10kHz		5.3		nV/√Hz
		>100kHz		3.5		nV/√Hz
DC Performance						
V _{IO}	Input Offset Voltage		-1	0.050	1	mV
d _{VIO}	Average Drift			1.3		μV/°C
I _B	Input Bias Current		-2.6	-0.30	2.6	μA
dI _B	Average Drift			0.85		nA/°C
I _{OS}	Input Offset Current			0.2	0.7	μA
PSRR	Power Supply Rejection Ratio	DC	82	100		dB
A _{OL}	Open Loop Gain	V _{OUT} = V _S / 2	95	115		dB
I _S	Supply Current	per channel		2.2	2.75	mA
Input Characteristics						
R _{IN}	Input Resistance	Non-inverting, G = 1		30		MΩ
C _{IN}	Input Capacitance			1		pF
CMIR	Common Mode Input Range			±5.5		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = -3V to 3V	70	95		dB
Output Characteristics						
V _{OUT}	Output Swing	R _L = 150Ω		-4.826 to 4.534		V
		R _L = 1kΩ	-4.7	-4.93 to 4.85	4.7	V
I _{OUT}	Output Current			+80, -55		mA
I _{SC}	Short Circuit Current	V _{OUT} = V _S / 2		+115, -90		mA

CLC1003 Pin Configurations

TSOT-5

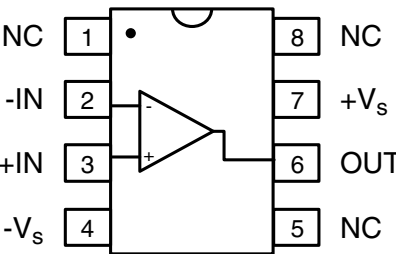


CLC1003 Pin Assignments

TSOT-5

Pin No.	Pin Name	Description
1	OUT	Output
2	-Vs	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+Vs	Positive supply

SOIC-8



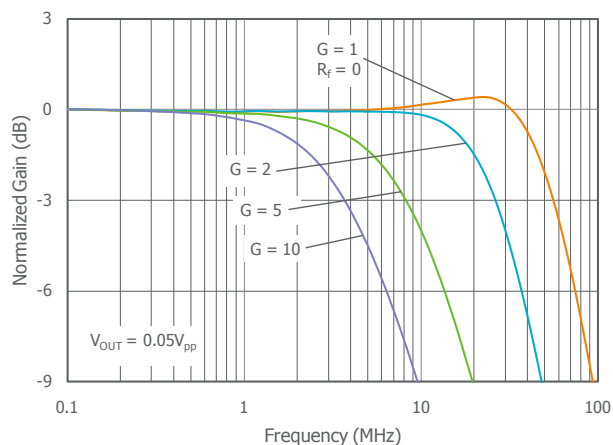
SOIC-8

Pin No.	Pin Name	Description
1	NC	No Connect
2	-IN	Negative input
3	+IN	Positive input
4	-Vs	Negative supply
5	NC	No Connect
6	OUT	Output
7	+Vs	Positive supply
8	NC	No Connect

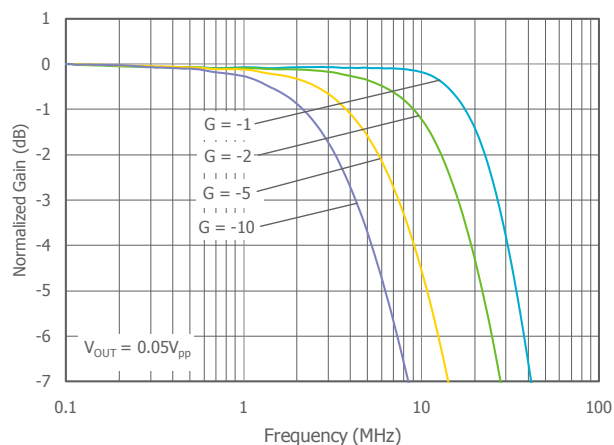
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = \pm 5\text{V}$, $R_f = 1\text{k}\Omega$, $R_L = 1\text{k}\Omega$, $G = 2$; unless otherwise noted.

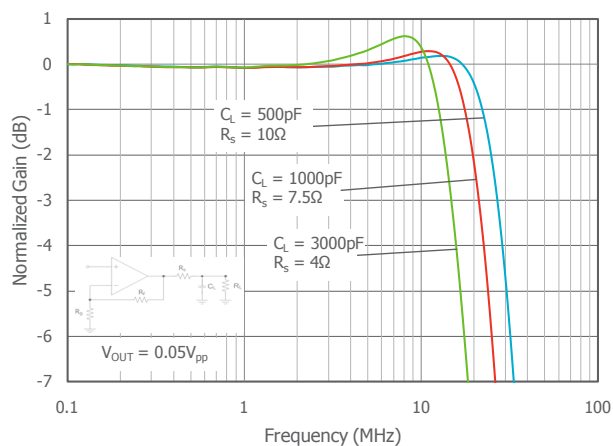
Non-Inverting Frequency Response



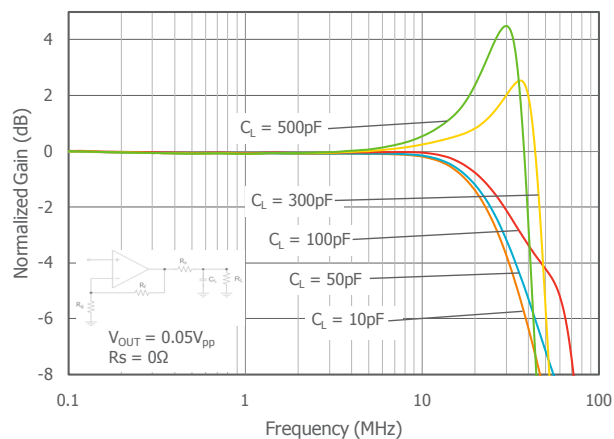
Inverting Frequency Response



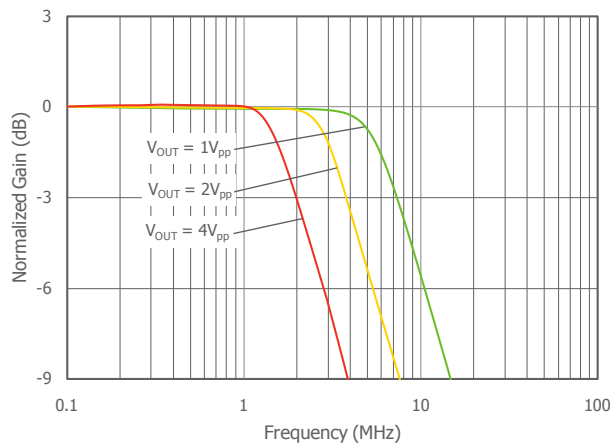
Frequency Response vs. C_L



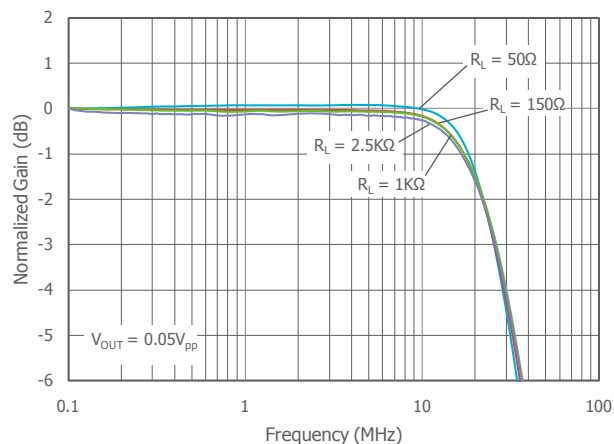
Frequency Response vs. C_L without R_S



Frequency Response vs. V_{OUT}



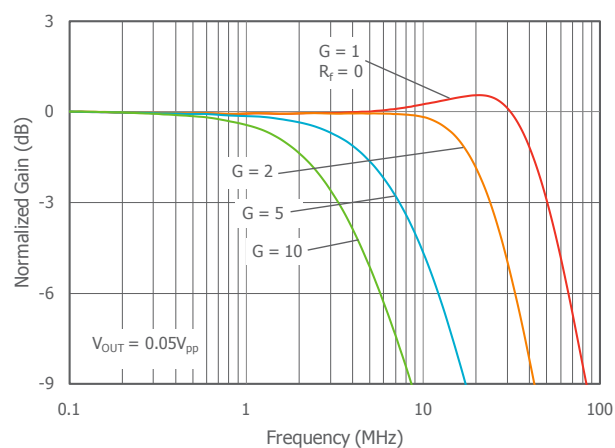
Frequency Response vs. R_L



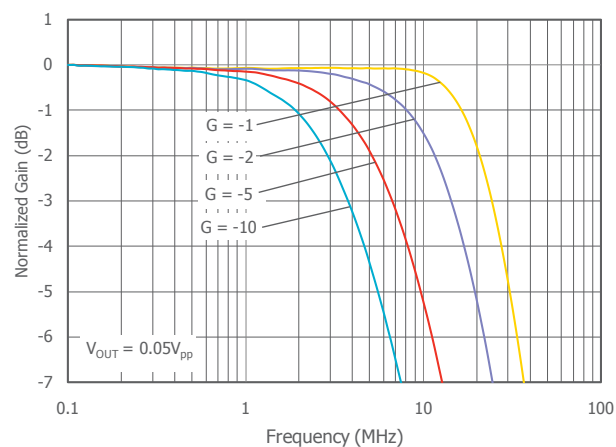
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = \pm 5\text{V}$, $R_f = 1\text{k}\Omega$, $R_L = 1\text{k}\Omega$, $G = 2$; unless otherwise noted.

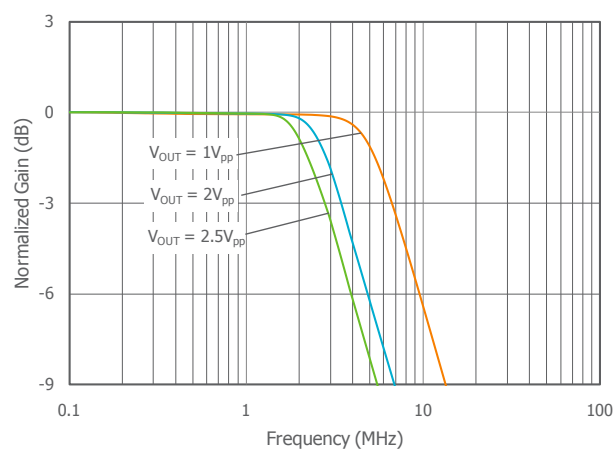
Non-Inverting Frequency Response at $V_S = 3\text{V}$



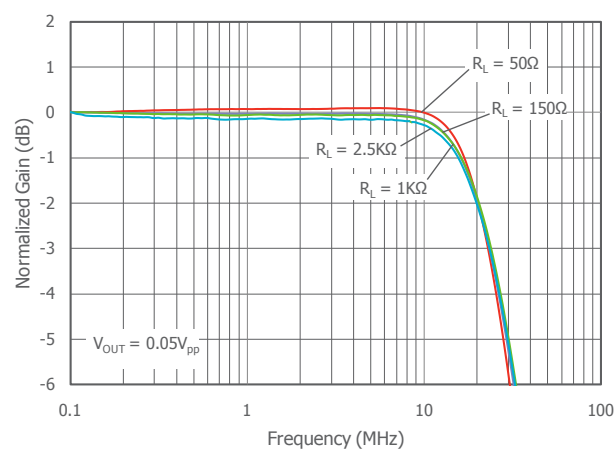
Inverting Frequency Response at $V_S = 3\text{V}$



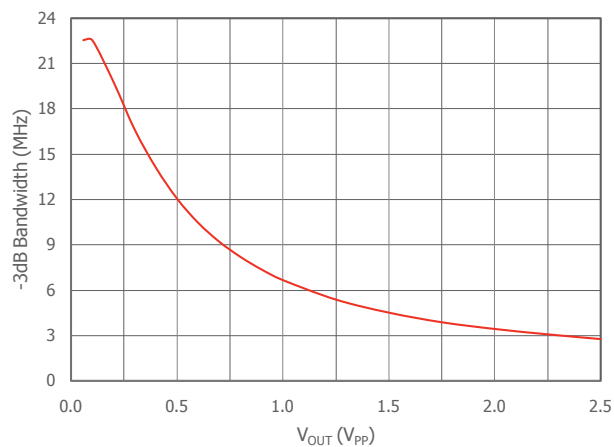
Frequency Response vs. V_{OUT} at $V_S = 3\text{V}$



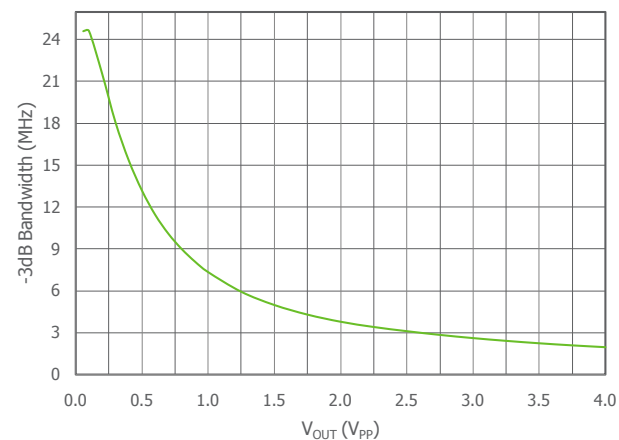
Frequency Response vs. R_L at $V_S = 3\text{V}$



-3dB Bandwidth vs. Output Voltage at $V_S = 3\text{V}$



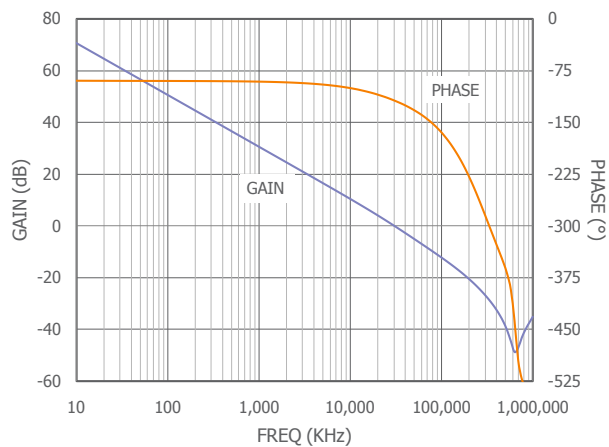
-3dB Bandwidth vs. Output Voltage



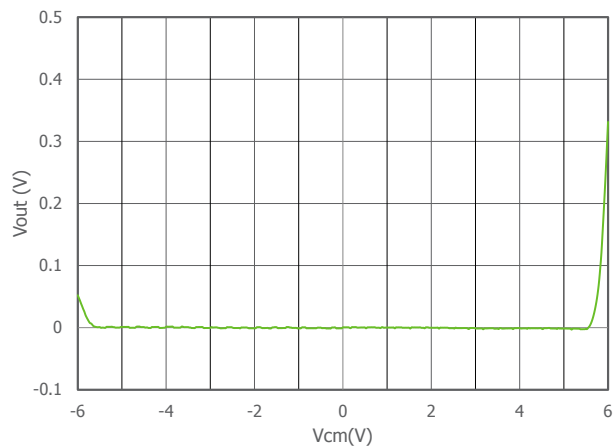
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = \pm 5\text{V}$, $R_f = 1\text{k}\Omega$, $R_L = 1\text{k}\Omega$, $G = 2$; unless otherwise noted.

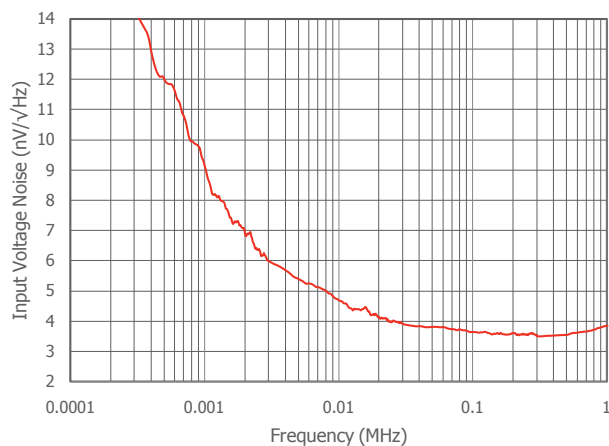
Open Loop Gain and Phase vs.



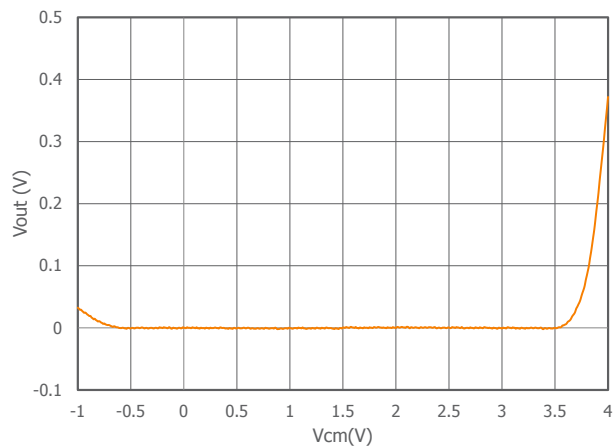
CMIR



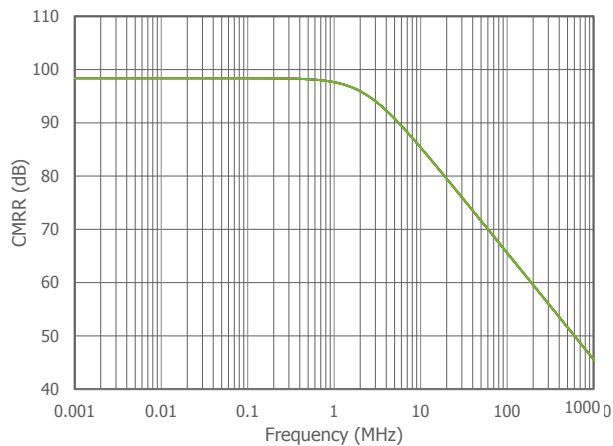
Input Voltage Noise



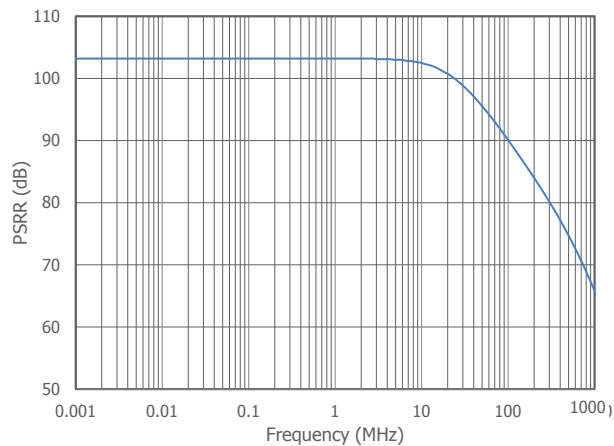
CMIR at $V_S = 3\text{V}$



CMRR vs. Frequency



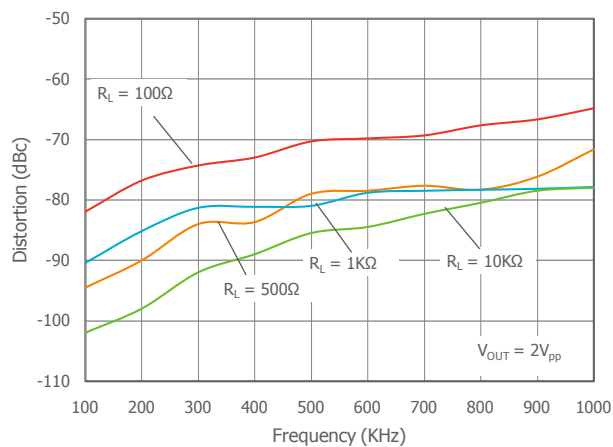
PSRR vs. Frequency



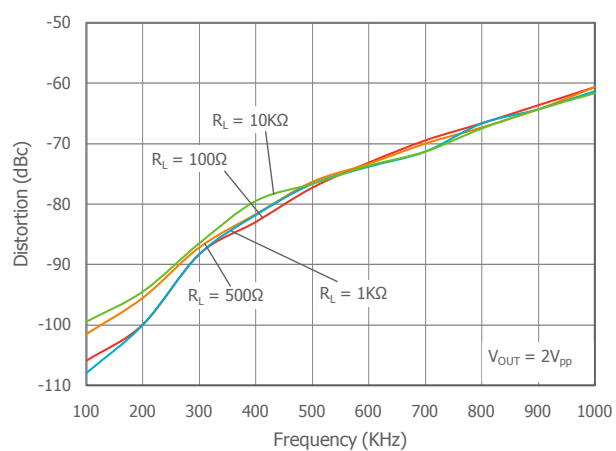
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = \pm 5\text{V}$, $R_f = 1\text{k}\Omega$, $R_L = 1\text{k}\Omega$, $G = 2$; unless otherwise noted.

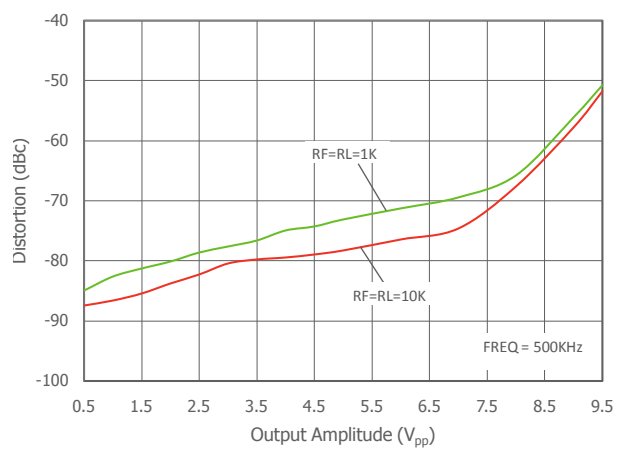
2nd Harmonic Distortion vs. R_L



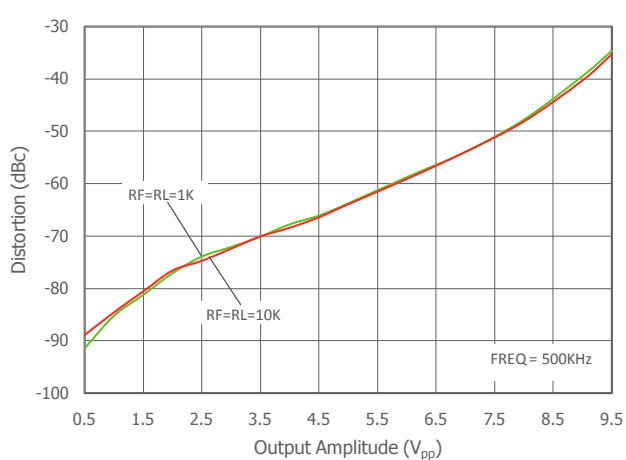
3rd Harmonic Distortion vs. R_L



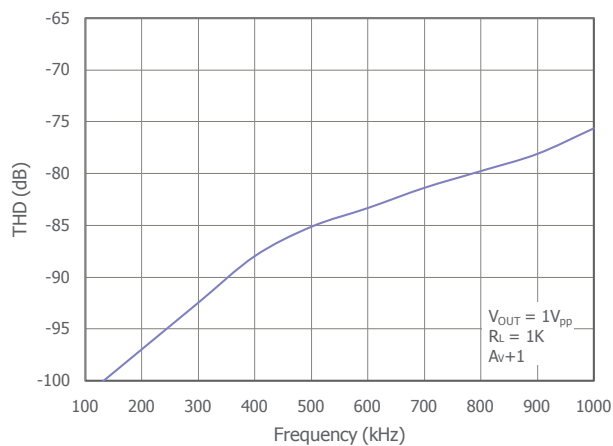
2nd Harmonic Distortion vs. V_{OUT}



3rd Harmonic Distortion vs. V_{OUT}



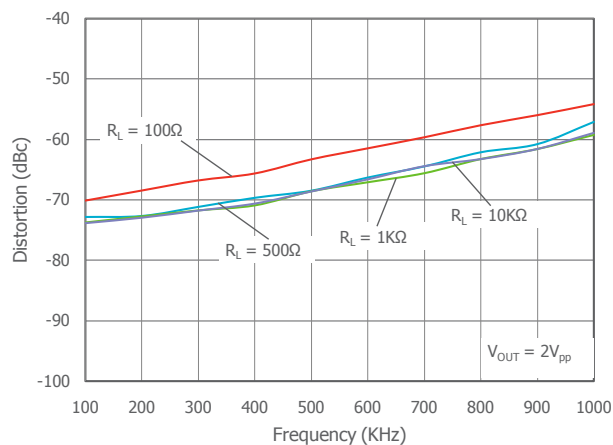
THD vs. Frequency



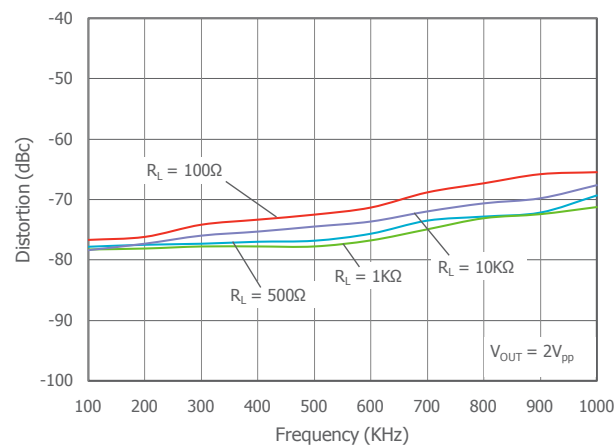
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = \pm 5\text{V}$, $R_f = 1\text{k}\Omega$, $R_L = 1\text{k}\Omega$, $G = 2$; unless otherwise noted.

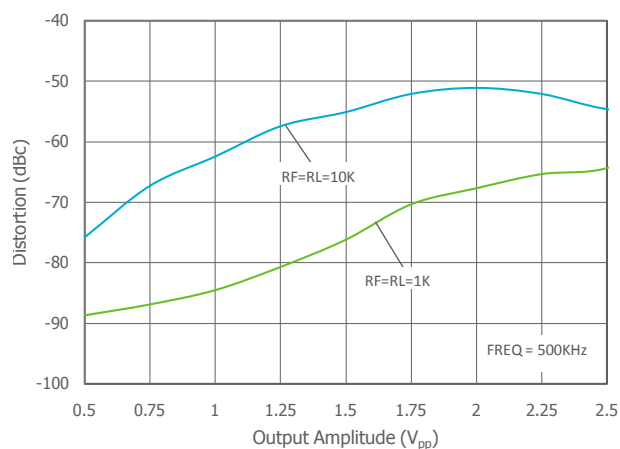
2nd Harmonic Distortion vs. R_L at $V_S = 3\text{V}$



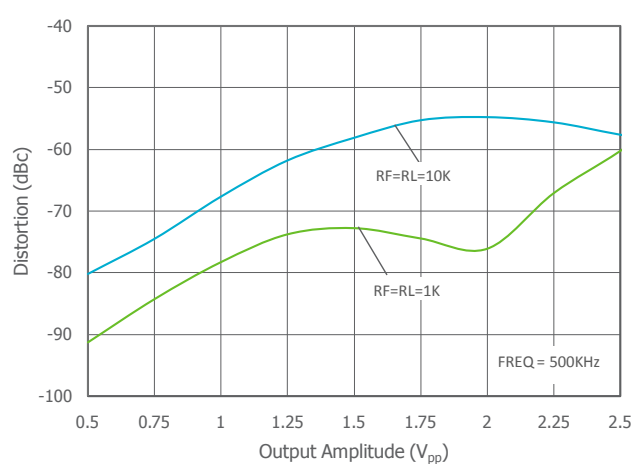
3rd Harmonic Distortion vs. R_L at $V_S = 3\text{V}$



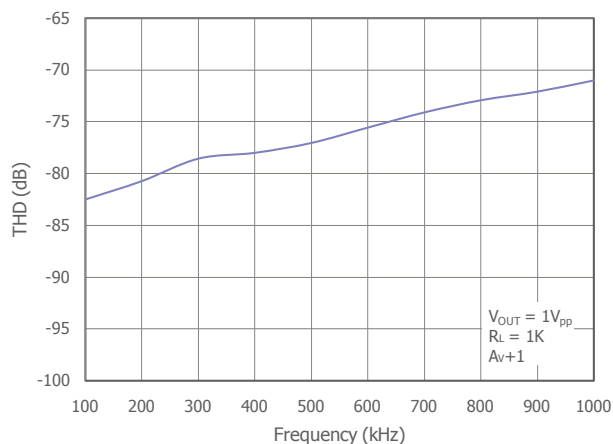
2nd Harmonic Distortion vs. V_{OUT} at $V_S = 3\text{V}$



3rd Harmonic Distortion vs. V_{OUT} at $V_S = 3\text{V}$



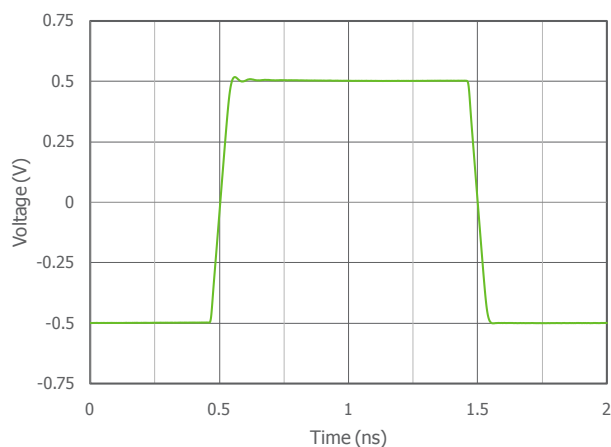
THD vs. Frequency at $V_S = 3\text{V}$



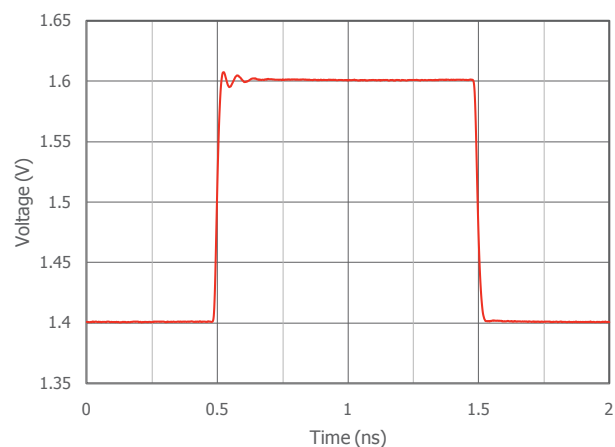
Typical Performance Characteristics

$T_A = 25^\circ\text{C}$, $V_S = \pm 5\text{V}$, $R_f = 1\text{k}\Omega$, $R_L = 1\text{k}\Omega$, $G = 2$; unless otherwise noted.

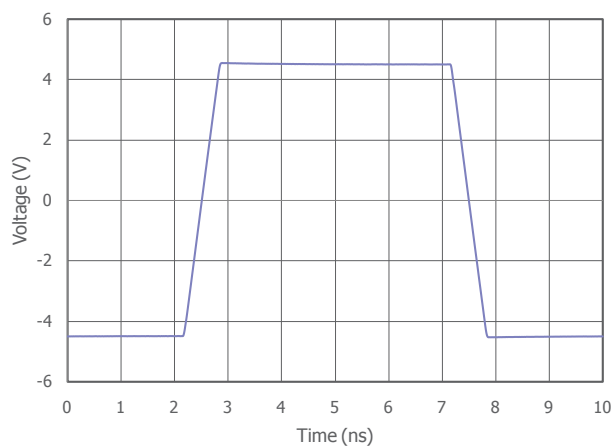
Small Signal Pulse Response



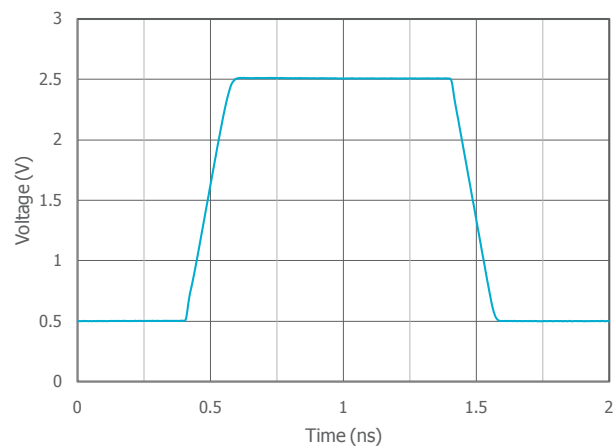
Small Signal Pulse Response at $V_S = 3\text{V}$



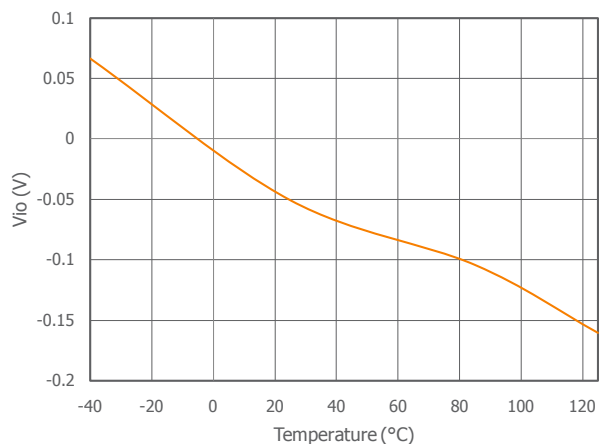
Large Signal Pulse Response



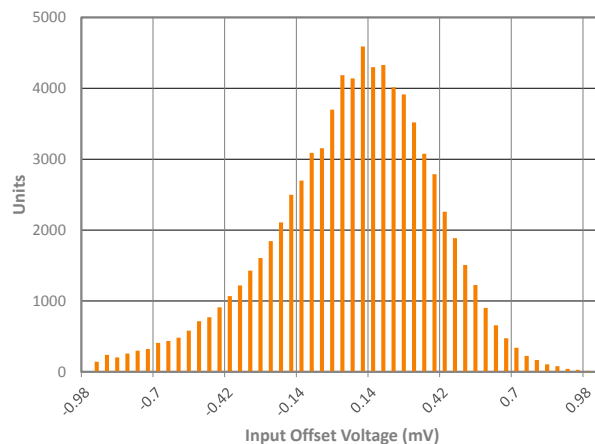
Large Signal Pulse Response at $V_S = 3\text{V}$



Input Offset Voltage vs. Temperature



Input Offset Voltage Distribution



Application Information

Basic Information

Figures 1 and 2 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations.

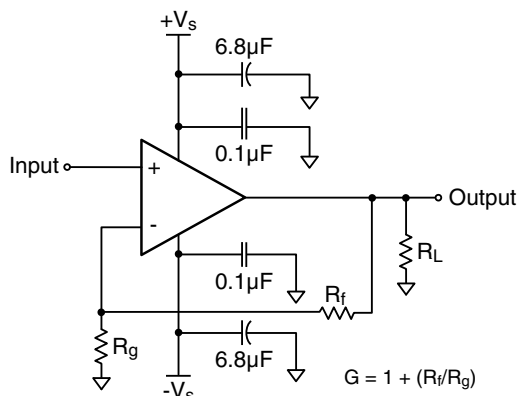


Figure 1: Typical Non-Inverting Gain Circuit

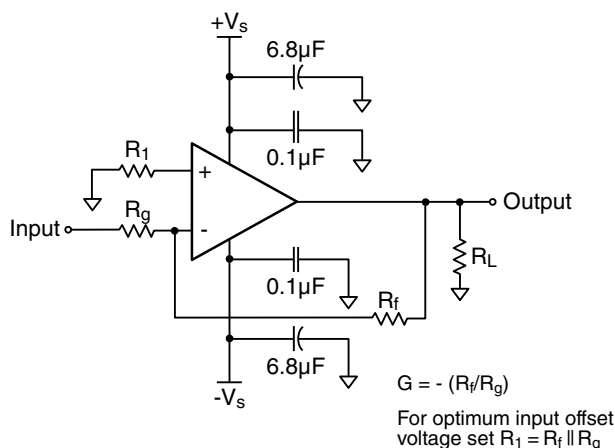


Figure 2: Typical Inverting Gain Circuit

Power Dissipation

Power dissipation should not be a factor when operating under the stated 500Ω load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond its intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 150°C. To calculate the junction temperature, the package thermal resistance value θ_{JA} (θ_{JA}) is used along with the total die power dissipation.

$$T_{\text{Junction}} = T_{\text{Ambient}} + (\theta_{JA} \times P_D)$$

Where T_{Ambient} is the temperature of the working environment.

In order to determine P_D , the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{\text{supply}} - P_{\text{load}}$$

Supply power is calculated by the standard power equation.

$$P_{\text{supply}} = V_{\text{supply}} \times I_{\text{RMSsupply}}$$

$$V_{\text{supply}} = V_{S+} - V_{S-}$$

Power delivered to a purely resistive load is:

$$P_{\text{load}} = ((V_{\text{load}})_{\text{RMS}}^2) / R_{\text{load eff}}$$

The effective load resistor ($R_{\text{load eff}}$) will need to include the effect of the feedback network. For instance,

$R_{\text{load eff}}$ in Figure 2 would be calculated as:

$$R_L \parallel (R_f + R_g)$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here, P_D can be found from

$$P_D = P_{\text{Quiescent}} + P_{\text{Dynamic}} - P_{\text{load}}$$

Quiescent power can be derived from the specified I_S values along with known supply voltage, V_{supply} . Load power can be calculated as above with the desired signal amplitudes using:

$$(V_{\text{load}})_{\text{RMS}} = V_{\text{peak}} / \sqrt{2}$$

$$(I_{\text{load}})_{\text{RMS}} = (V_{\text{load}})_{\text{RMS}} / R_{\text{load eff}}$$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

$$P_{\text{Dynamic}} = (V_{S+} - V_{\text{load}})_{\text{RMS}} \times (I_{\text{load}})_{\text{RMS}}$$

Assuming the load is referenced in the middle of the power rails or $V_{\text{supply}}/2$.

Figure 3 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

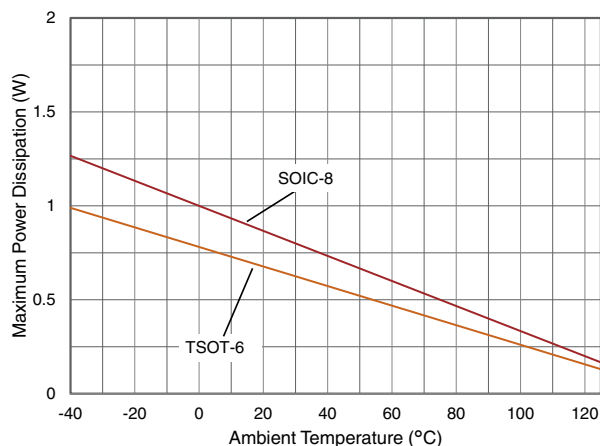
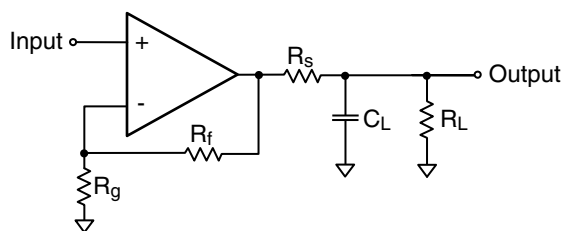


Figure 3. Maximum Power Derating

Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, R_S , between the amplifier and the load to help improve stability and settling performance. Refer to Figure 4.

Figure 4. Addition of R_S for Driving Capacitive Loads

The CLC1003 is capable of driving up to 300pF directly, with no series resistance. Directly driving 500pF causes over 4dB of frequency peaking, as shown in the plot on page 6. Table 1 provides the recommended R_S for various capacitive loads. The recommended R_S values result in ≤ 1 dB peaking in the frequency response. The Frequency Response vs. C_L plots, on page 6, illustrate the response of the CLC1003.

C_L (pF)	R_S (Ω)	-3dB BW (MHz)
500	10	27
1000	7.5	20
3000	4	15

Table 1: Recommended R_S vs. C_L

For a given load capacitance, adjust R_S to optimize the tradeoff between settling time and bandwidth. In general, reducing R_S will increase bandwidth at the expense of additional overshoot and ringing.

Overdrive Recovery

An overdrive condition is defined as the point when either one of the inputs or the output exceed their specified voltage range. Overdrive recovery is the time needed for the amplifier to return to its normal or linear operating point. The recovery time varies based on whether the input or output is overdriven and by how much the ranges are exceeded. The CLC1003 will typically recover in less than 20ns from an overdrive condition. Figure 5 shows the CLC1003 in an overdriven condition.

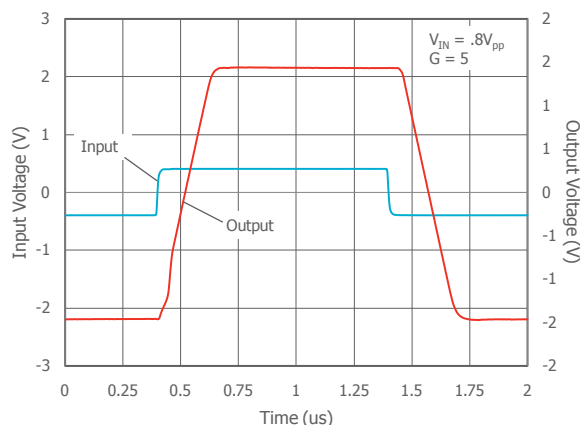


Figure 5: Overdrive Recovery

Considerations for Offset and Noise Performance

Offset Analysis

There are three sources of offset contribution to consider; input bias current, input bias current mismatch, and input offset voltage. The input bias currents are assumed to be equal with and additional offset current in one of the inputs to account for mismatch. The bias currents will not affect the offset as long as the parallel combination of R_f and R_g matches R_t . Refer to Figure 6.

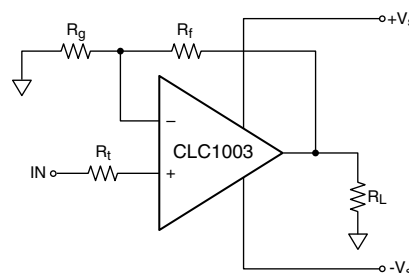


Figure 6: Circuit for Evaluating Offset

The first place to start is to determine the source resistance. If it is very small an additional resistance may need to be added to keep the values of R_f and R_g to practical levels. For this analysis we assume that R_t is the total resistance present on the non-inverting input. This gives us one equation that we must solve:

$$R_t = R_g \parallel R_f$$

This equation can be rearranged to solve for R_g :

$$R_g = (R_t * R_f) / (R_f - R_t)$$

The other consideration is desired gain (G) which is:

$$G = (1 + R_f/R_g)$$

By plugging in the value for R_g we get

$$R_f = G * R_t$$

And R_g can be written in terms of R_t and G as follows:

$$R_g = (G * R_t) / (G - 1)$$

The complete input offset equation is now only dependent on the voltage offset and input offset terms given by:

$$V_{IOS} = \sqrt{(V_{IO})^2 + (I_{OS} * RT)^2}$$

And the output offset is:

$$VO_{OS} = G * \sqrt{(V_{IO})^2 + (I_{OS} * RT)^2}$$

Noise analysis

The complete equivalent noise circuit is shown in Figure 7.

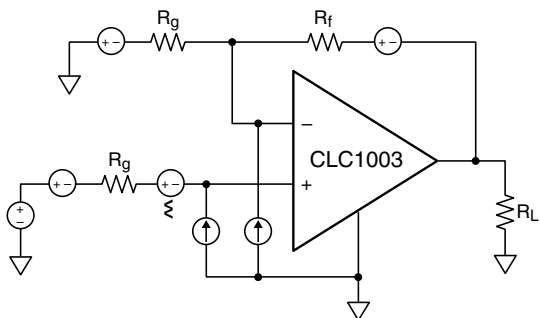


Figure 7: Complete Equivalent Noise Circuit

The complete noise equation is given by:

$$v_o^2 = v_{orext}^2 + \left(e_n \left(1 + \frac{R_f}{R_g} \right) \right)^2 + \left(i_{bp} * RT \left(1 + \frac{R_f}{R_g} \right) \right)^2 + \left(i_{bn} * R_f \right)^2$$

Where V_{orext} is the noise due to the external resistors and is given by:

$$v_o^2 = \left(e_n \left(1 + \frac{R_f}{R_g} \right) \right)^2 + \left(e_G * \frac{R_f}{R_g} \right)^2 + e_F^2$$

The complete equation can be simplified to:

$$v_o^2 = 3 * (4kT * G * RT) + (e_n G)^2 + 2 * (i_n * RT)^2$$

It's easy to see that the effect of amplifier voltage noise is proportionate to gain and will tend to dominate at large gains. The other terms will have their greatest impact at large R_t values at lower gains.

Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. Exar has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8μF and 0.1μF ceramic capacitors for power supply decoupling
- Place the 6.8μF capacitor within 0.75 inches of the power pin
- Place the 0.1μF capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

Evaluation Board Information

The following evaluation boards are available to aid in the testing and layout of these devices:

Evaluation Board #	Products
CEB002	CLC1003 in TSOT
CEB003	CLC1003 in SOIC

Evaluation Board Schematics

Evaluation board schematics and layouts are shown in Figures 8-12. These evaluation boards are built for dual-supply operation. Follow these steps to use the board in a single-supply application:

1. Short $-V_S$ to ground.
2. Use C3 and C4, if the $-V_S$ pin of the amplifier is not directly connected to the ground plane.

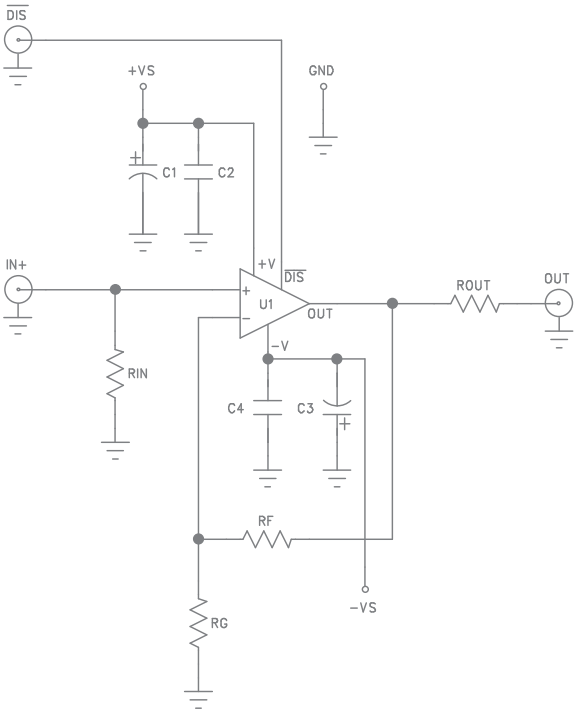


Figure 8. CEB002 & CEB003 Schematic

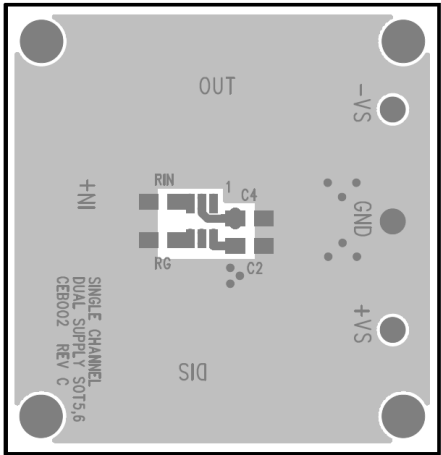


Figure 9. CEB002 Top View

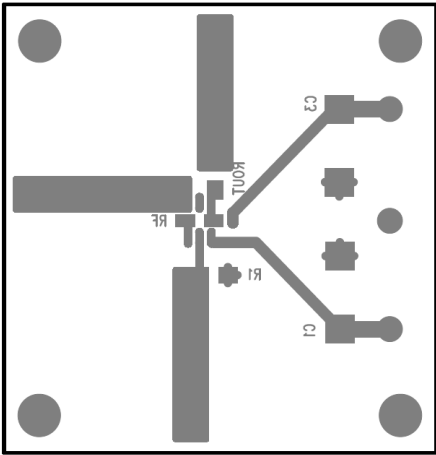


Figure 10. CEB002 Bottom View

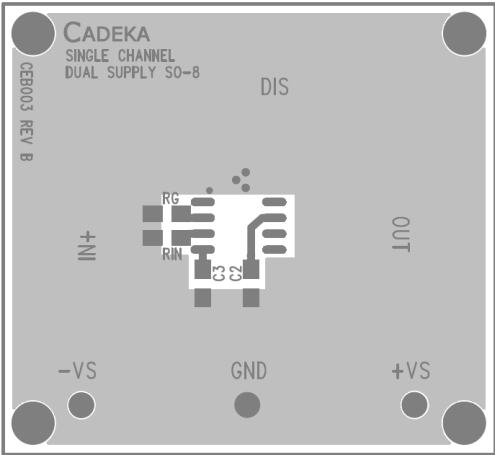


Figure 11. CEB003 Top View

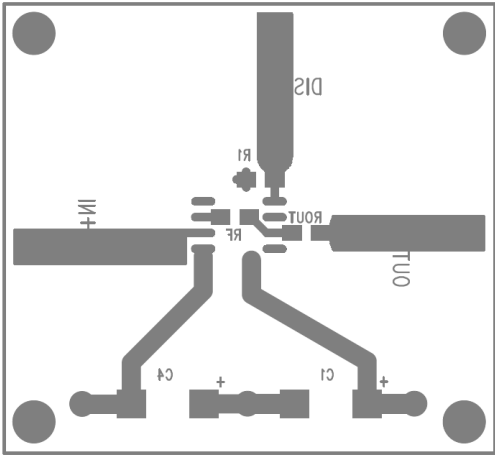
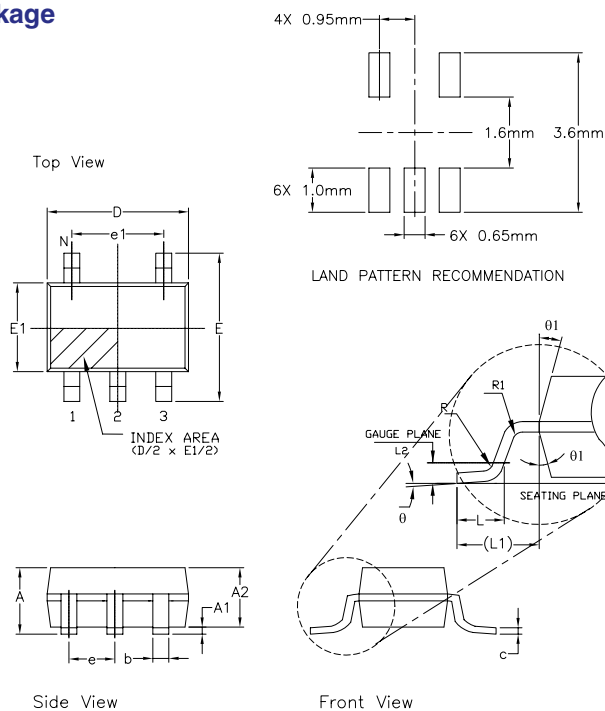


Figure 12. CEB003 Bottom View

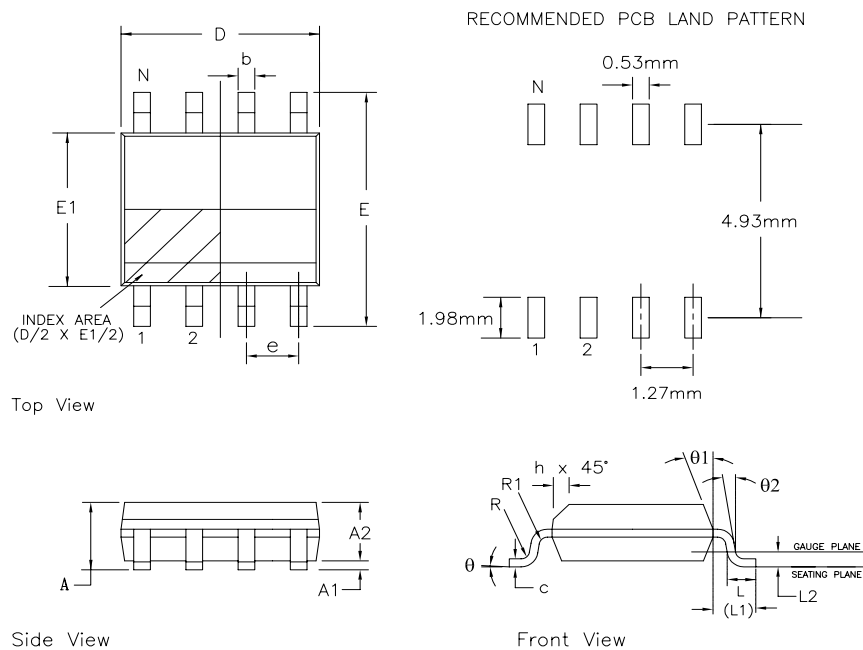
Mechanical Dimensions

TSOT-5 Package



5 Pin TSOT (OPTION 2)						
SYMBOLS	DIMENSION IN MM (Control Unit)			DIMENSION IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.75	—	0.80	0.030	—	0.031
A1	0.00	—	0.05	0.000	—	0.002
A2	0.70	0.75	0.78	0.028	0.030	0.031
b	0.35	—	0.50	0.012	—	0.020
c	0.10	—	0.20	0.003	—	0.008
D	2.90 BSC			0.114 BSC		
E	2.80 BSC			0.110 BSC		
E1	1.60 BSC			0.063 BSC		
e	0.95 BSC			0.038 BSC		
e1	1.90 BSC			0.075 BSC		
L	0.37	0.45	0.60	0.012	0.018	0.024
L1	0.60 REF			0.024 REF		
L2	0.25 BSC			0.010 BSC		
R	0.10	—	—	0.004	—	—
R1	0.10	—	0.25	0.004	—	0.010
θ	0°	4°	8°	0°	4°	8°
θ1	4°	10°	12°	4°	10°	12°
N	5			5		

SOIC-8 Package



8 Pin SOICN JEDEC MS-012 Variation AA						
SYMBOLS	DIMENSIONS IN MM (Control Unit)			DIMENSIONS IN INCH (Reference Unit)		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.35	—	1.75	0.053	—	0.069
A1	0.10	—	0.25	0.004	—	0.010
A2	1.25	—	1.65	0.049	—	0.065
b	0.31	—	0.51	0.012	—	0.020
c	0.17	—	0.25	0.007	—	0.010
E	6.00 BSC			0.236 BSC		
E1	3.90 BSC			0.154 BSC		
e	1.27 BSC			0.050 BSC		
h	0.25	—	0.50	0.010	—	0.020
L	0.40	—	1.27	0.016	—	0.050
L1	1.04 REF			0.041 REF		
L2	0.25 BSC			0.010 BSC		
R	0.07	—	—	0.003	—	—
R1	0.07	—	—	0.003	—	—
θ	0°	—	8°	0°	—	8°
θ1	5°	—	15°	5°	—	15°
θ2	0°	—	—	0°	—	—
D	4.90 BSC			0.193 BSC		
N	8			8		

Ordering Information

Part Number	Package	Green	Operating Temperature Range	Packaging Quantity
CLC1003 Ordering Information				
CLC1003IST5X*	TSOT-5	Yes	-40°C to +125°C	2.5k Tape & Reel
CLC1003IST5MTR*	TSOT-5	Yes	-40°C to +125°C	250 Tape & Reel
CLC1003IST5EVB*	Evaluation Board	N/A	N/A	N/A
CLC1003ISO8X	SOIC-8	Yes	-40°C to +125°C	2.5k Tape & Reel
CLC1003ISO8MTR	SOIC-8	Yes	-40°C to +125°C	250 Tape & Reel
CLC1003ISO8EVB	Evaluation Board	N/A	N/A	N/A

Moisture sensitivity level for all parts is MSL-1.

*Contact Resurgent Semiconductor for availability.

Revision History

Revision	Date	Description
1D (ECN 1441-07)	September 2014	Reformat into Exar data sheet template. Updated ordering information table to include MTR and EVB part numbers. Increased "I" temperature range from +85 to +125°C. Removed "A" temp grade parts, since "I" is now equivalent. Updated thermal resistance numbers and package outline drawings.
1D.R	July 2018	Updated to Resurgent Semiconductor.

For Further Assistance:

www.resurgentsemi.net



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